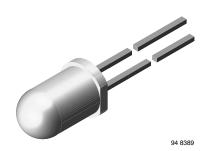
TSHG8200



Vishay Semiconductors

High Speed Infrared Emitting Diode, 830 nm, GaAlAs Double Hetero



DESCRIPTION

TSHG8200 is an infrared, 830 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- · Package type: leaded
- Package form: T-1³/₄
- Dimensions (in mm): $\varnothing\,5$
- Peak wavelength: $\lambda_p = 830 \text{ nm}$
- · High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\phi = \pm 10^{\circ}$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: f_c = 18 MHz
- · Good spectral matching with CMOS cameras
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

Note

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras (illumination)
- High speed IR data transmission
- · Smoke-automatic fire detectors

PRODUCT SUMMARY					
COMPONENT	l _e (mW/sr)	φ (deg)	λ _P (nm)	tr (ns)	
TSHG8200	180	± 10	830	20	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSHG8200	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾	

Note

• MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	1	А	
Power dissipation		Pv	180	mW	
Junction temperature		Тj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T _{sd}	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R _{thJA}	230	K/W	

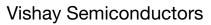
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(PQ) (e3) RoHS

COMPLIANT GREEN

(5-2008)**





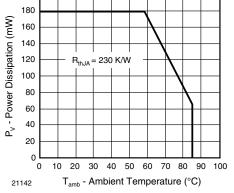


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

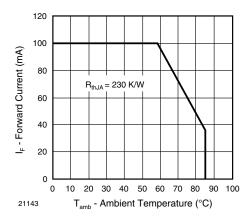


Fig. 1 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	l _F = 100 mA, t _p = 20 ms	V _F		1.5	1.8	V
	I _F = 1 A, t _p = 100 μs	V _F		2.3		V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj		125		pF
	l _F = 100 mA, t _p = 20 ms	l _e	120	180	360	mW/sr
Radiant intensity	I _F = 1 A, t _p = 100 μs	l _e		1600		mW/sr
Radiant power	l _F = 100 mA, t _p = 20 ms	φ _e		50		mW
Temperature coefficient of ϕ_{e}	I _F = 100 mA	TKφ _e		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I _F = 100 mA	λρ		830		nm
Spectral bandwidth	I _F = 100 mA	Δλ		40		nm
Temperature coefficient of λ_p	I _F = 100 mA	ΤΚλρ		0.25		nm/K
Rise time	I _F = 100 mA	t _r		20		ns
Fall time	I _F = 100 mA	t _f		13		ns
Cut-off frequency	$I_{DC} = 70$ mA, $I_{AC} = 30$ mA pp	f _c		18		MHz
Virtual source diameter		d		3.7		mm

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BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

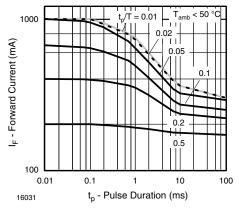


Fig. 2 - Pulse Forward Current vs. Pulse Duration

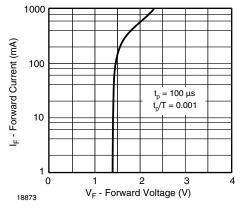


Fig. 3 - Forward Current vs. Forward Voltage

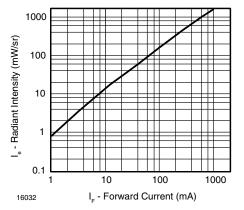


Fig. 4 - Radiant Intensity vs. Forward Current

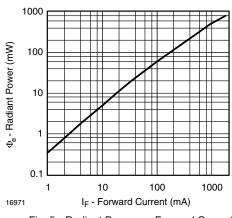


Fig. 5 - Radiant Power vs. Forward Current

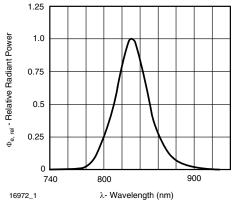


Fig. 6 - Relative Radiant Power vs. Wavelength

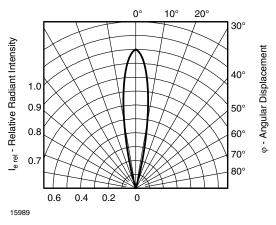


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

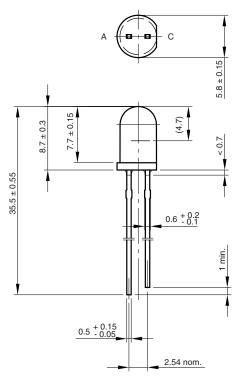
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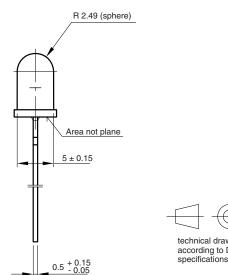


TSHG8200

Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters







according to DIN specifications

6.544-5259.02-4 Issue: 8; 19.05.09 95 10917



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